

IN THE CLAIMS:

Please replace claim 7 with the following rewritten clean version:

7. (Amended) A thin film transistor comprising a semiconductor film, a first gate insulating film, a second gate insulating film and a gate electrode sequentially formed in that order on one major surface of a substrate,

wherein said first gate insulating film covers said one major surface of the substrate and all regions of said semiconductor film other than a contact region, and

said second gate insulating film is made of a material for supplying hydrogen to said semiconductor film and is formed only in a region covered by said gate electrode to have substantially the same shape as said gate electrode.